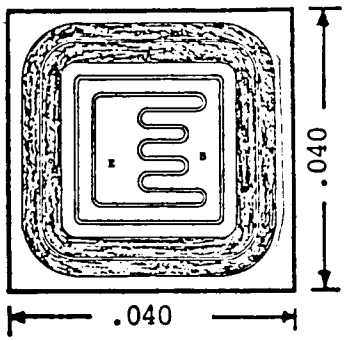
PRELIMINARY DATA SHEET 5-8-85

X00221

STX725 CHIP

HIGH VOLTAGE NPN TRANSISTOR CHIP



Contact Area: .005 x .005

CONTACT METALLIZATION

Base/Emitter: > 30,000 Å Aluminum

Collector: > 2,000 Å Evaporated Gold

ASSEMBLY RECOMMENDATIONS

1. Eutectic Die Attach.
2. Ultrasonically Attach 2 MIL Aluminum Wire To Base/Emitter Contacts.

PARAMETER	TEST CONDITIONS	TYPE	MIN.	MAX.	UNIT
BV_{CEO}	IC = 1 mA (pulsed)		450		Vdc
BV_{CBO}	IC = 100 uA		600		Vdc
BV_{CER}	IC = 100 uA, RBE= 5 K Ohm		600		Vdc
BV_{EBO}	IE = 20 uA		6		Vdc
I_{EBO}	VEB = 4 V			250	n Adc
I_{CBO}	VCB = 500 V			500	n Adc
h_{FE}	VCE = 10 V, IC = 1 mA		25	250	
h_{FE}	VCE = 5 V, IC = 25 mA		50	300	
h_{FE}	VCE = 5 V, IC= 100 mA		15	250	
$V_{BE(SAT)}$	IC = 25 mA, VCE = 5 V			1.0	Vdc
$V_{CE(SAT)}$	IC = 25 mA, IB= 2.5 mA			500	m Vdc
C_{OB}	VCB = 15 V			15	pf
f_T	VCE = 10 V, IC = 50 mA f = 20 MHz		25		MHz

Electrical characteristics measured at lot acceptance testing in a TO-5 package. Specifications subject to change without notice.

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